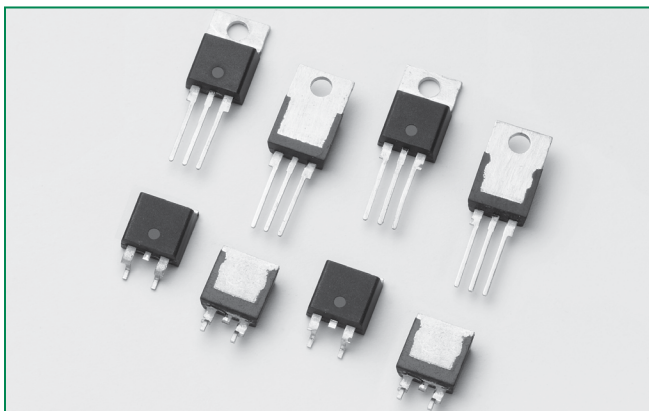


Qxx12xHx Series



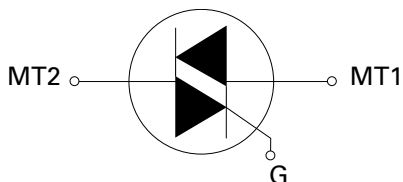
Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT}(Q1)$	10 to 50	mA

Schematic Symbol



Description

12 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 120 A
- Electrically isolated “L-Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, lawn care equipment, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Additional Information



Datasheet



Resources



Samples

Absolute Maximum Ratings — Alternistor (3 Quadrants)

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	Qxx12LHy	T _c = 90°C	12	A
		Qxx12RHy Qxx12NH _y	T _c = 105°C		
I _{TSM}	Non repetitive surge peak on-state current (full cycle, T _J initial = 25°C)	f = 50 Hz	t = 20 ms	110	A
		f = 60 Hz	t = 16.7 ms	120	
I ² t	I ² t Value for fusing		t _p = 8.3 ms	60	A ² s
di/dt	Critical rate of rise of on-state current	f = 120 Hz	T _J = 125°C	70	A/μs
I _{GTM}	Peak gate trigger current	t _g ≤ 10 μs; I _{GT} ≤ I _{GTM}	T _J = 125°C	2.0	A
P _{G(AV)}	Average gate power dissipation		T _J = 125°C	0.5	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 125	°C

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant		Qxx12xH2	Qxx12xH5	Unit
I _{GT}	V _D = 12V R _L = 60 Ω	I – II – III	MAX.	10	50	mA
V _{GT}		I – II – III	MAX.	1.3	1.3	V
V _{GD}	V _D = V _{DRM} R _L = 3.3 kΩ T _J = 125°C	I – II – III	MIN.	0.2	0.2	V
I _H	I _T = 100mA		MAX.	15	50	mA
dv/dt	V _D = V _{DRM} Gate Open T _J = 125°C	400V	MIN.	300	750	V/μs
		600V		200	650	
		800V		150	500	
	V _D = V _{DRM} Gate Open T _J = 100°C	1000V		150	300	
(dv/dt)c	(di/dt)c = 6.5 A/ms T _J = 125°C		MIN.	2	30	V/μs
t _{gt}	I _G = 2 x I _{GT} PW = 15μs I _T = 17.0 A(pk)		TYP.	4	4	μs

Static Characteristics

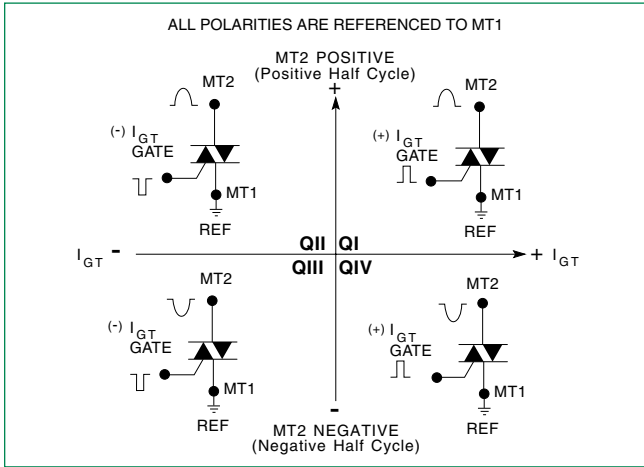
Symbol	Test Conditions				Value	Unit
V _{TM}	I _{TM} = 17.0A t _p = 380 μs			MAX.	1.60	V
I _{DRM} I _{RRM}	V _D = V _{DRM} / V _{RRM}	T _J = 25°C	400-1000V	MAX.	10	μA
		T _J = 125°C	400-800V		2	mA
		T _J = 100°C	1000V		3	

Thermal Resistances

Symbol	Parameter		Value	Unit
R _{θ(J-C)}	Junction to case (AC)	Qxx12RHy Qxx12NH _y	1.2	°C/W
		Qxx12LHy	2.3	
R _{θ(J-A)}	Junction to ambient (AC)	Qxx12RHy	45	°C/W
		Qxx12LHy	90	

ote: xx = voltage, y = sensitivity

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

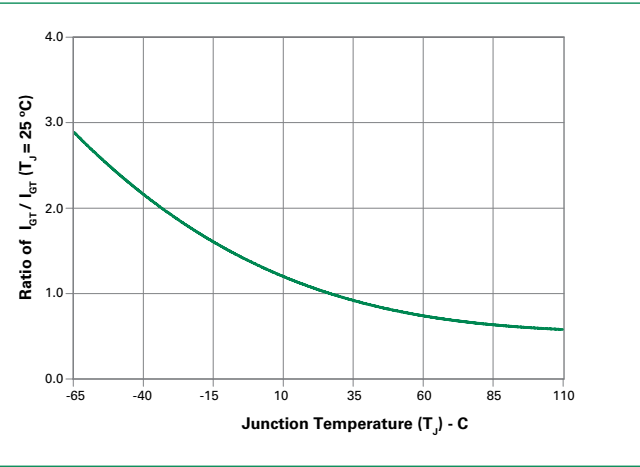


Figure 3: Normalized DC Holding Current vs. Junction Temperature

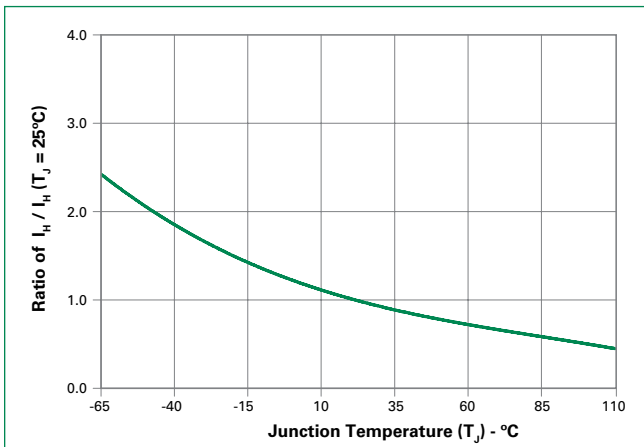


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

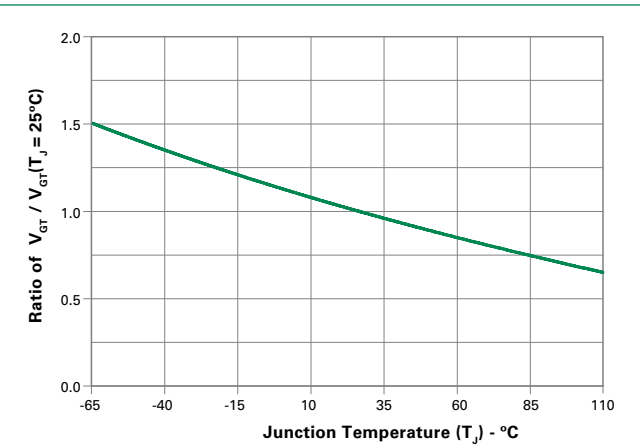


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

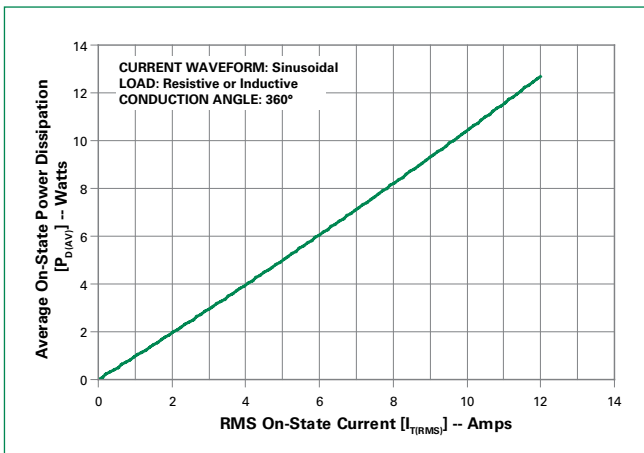


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

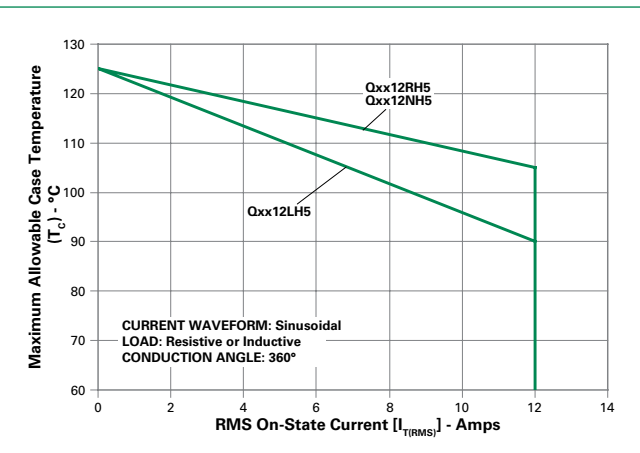


Figure 7: Maximum Allowable Ambient Temperature vs. On-State Current

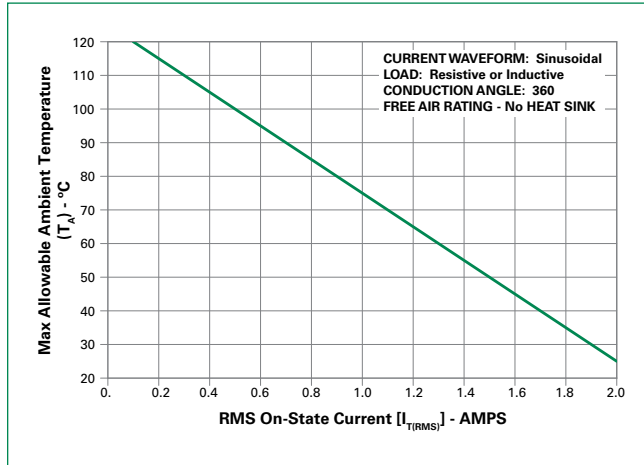


Figure 8: On-State Current vs. On-State Voltage (Typical)

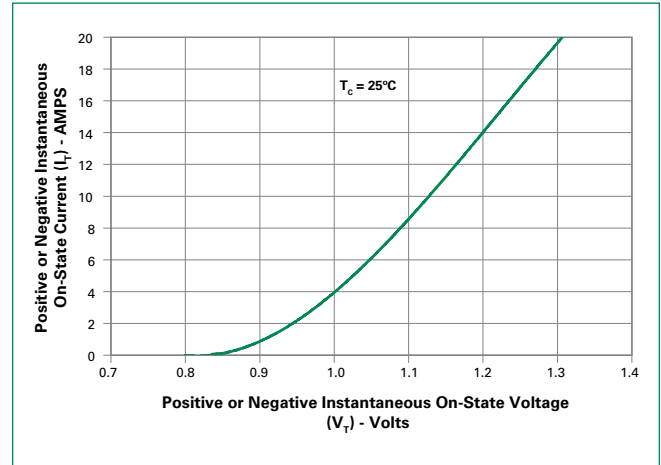
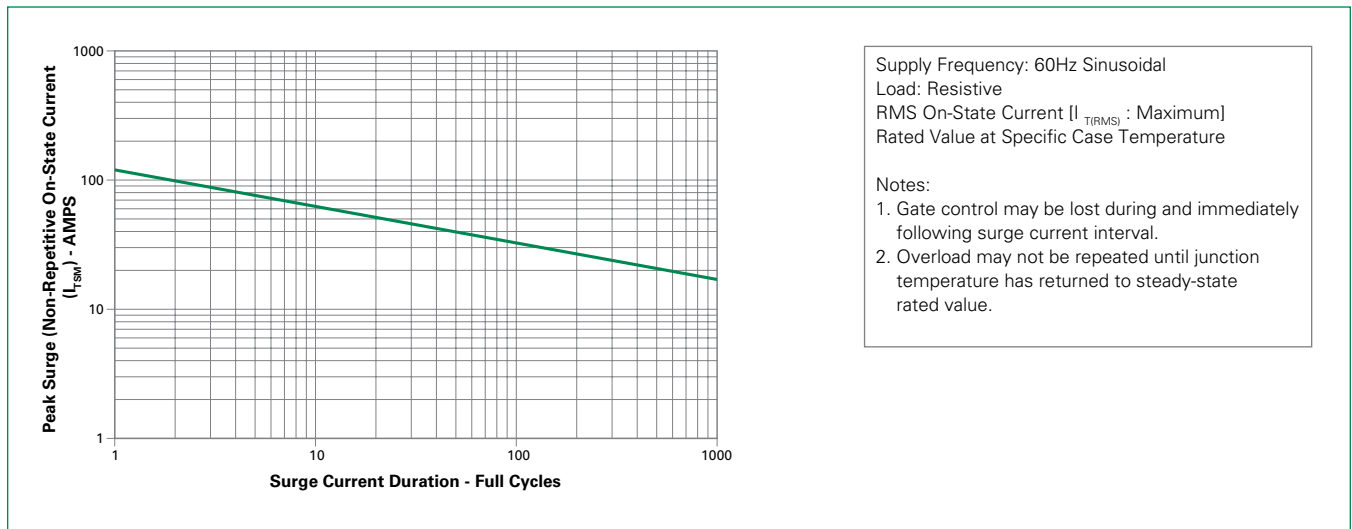
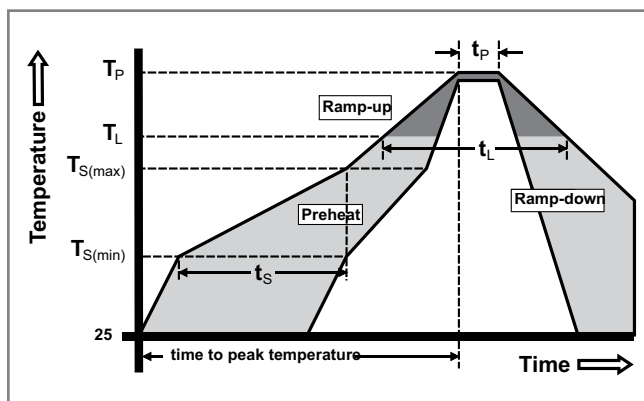


Figure 9: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

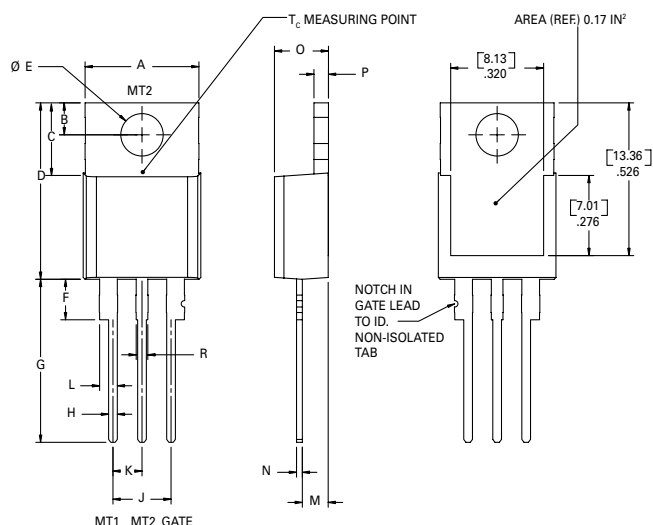
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

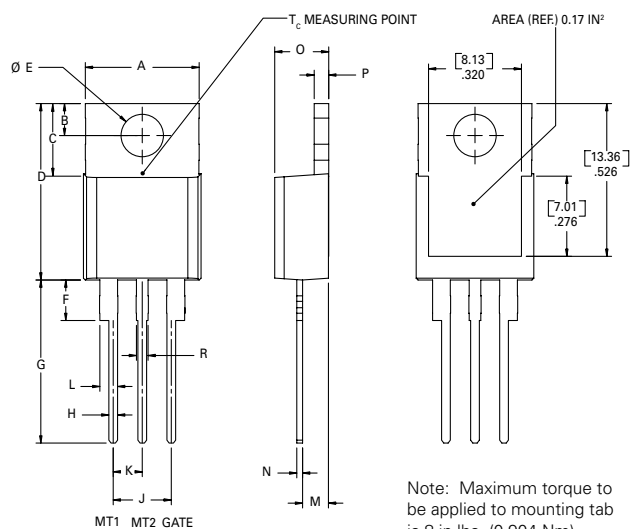
Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

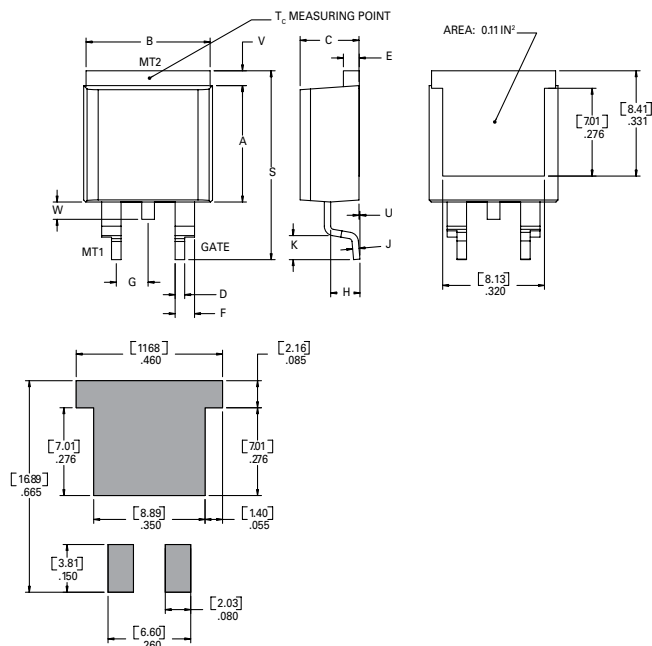
Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-263AB (N-Package) — D²Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Product Selector

Part Number	Voltage				Gate Sensitivity Quadrants I – II – III	Type	Package
	400V	600V	800V	1000V			
Qxx12LH2	X	X	X		10 mA	Alternistor Triac	TO-220L
Qxx12RH2	X	X	X		10 mA	Alternistor Triac	TO-220R
Qxx12NH2	X	X	X		10 mA	Alternistor Triac	TO-263 D ² PAK
Qxx12LH5	X	X	X	X	50 mA	Alternistor Triac	TO-220L
Qxx12RH5	X	X	X	X	50 mA	Alternistor Triac	TO-220R
Qxx12NH5	X	X	X	X	50 mA	Alternistor Triac	TO-263 D ² PAK

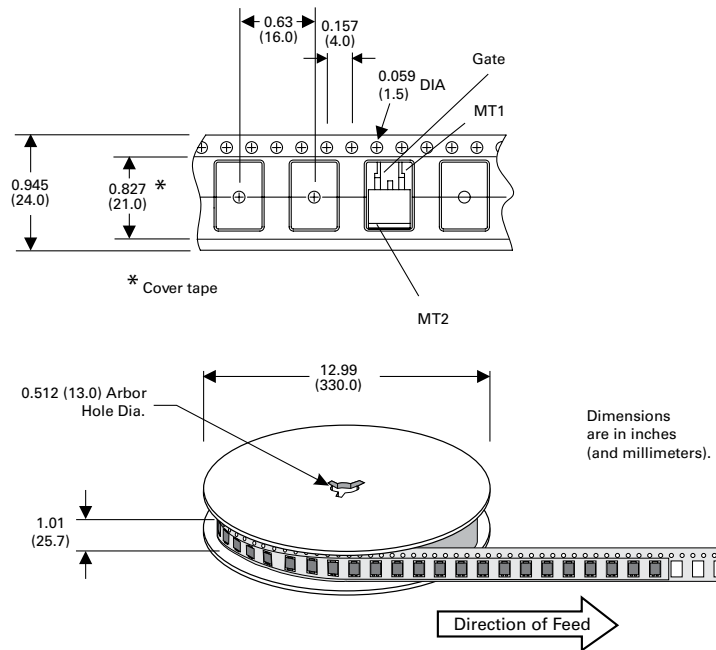
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx12L/RHy	Qxx12L/RHy	2.2 g	Bulk	500
Qxx12L/RHyTP	Qxx12L/RHy	2.2 g	Tube Pack	500 (50 per tube)
Qxx12NHyTP	Qxx12NHy	1.6 g	Tube	500 (50 per tube)
Qxx12NHyRP	Qxx12NHy	1.6 g	Embossed Carrier	500

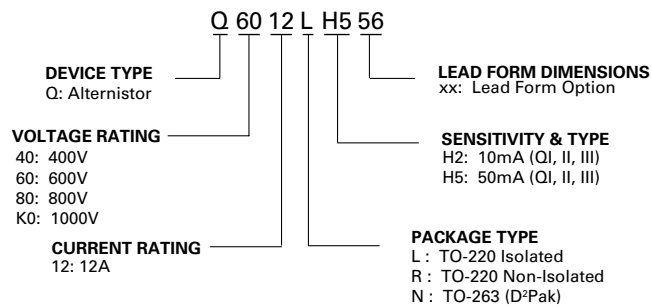
Note: xx = Voltage; y = Sensitivity

TO-263 Embossed Carrier Reel Pack (RP)

Meets all EIA-481-2 Standards

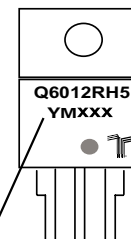


Part Numbering System



Part Marking System

TO-220 AB - (L and R Package)
TO-263 AB - (N Package)



Date Code Marking
Y: Year Code
M: Month Code
XXX: Lot Trace Code



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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